

Supporting Information

Interface engineering for gain perovskite photodetectors with an extremely high external quantum efficiency

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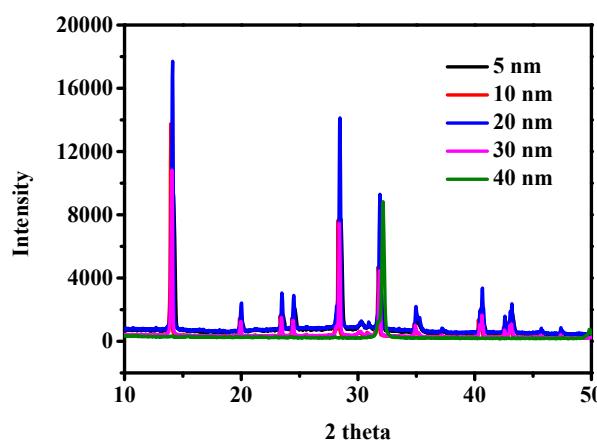
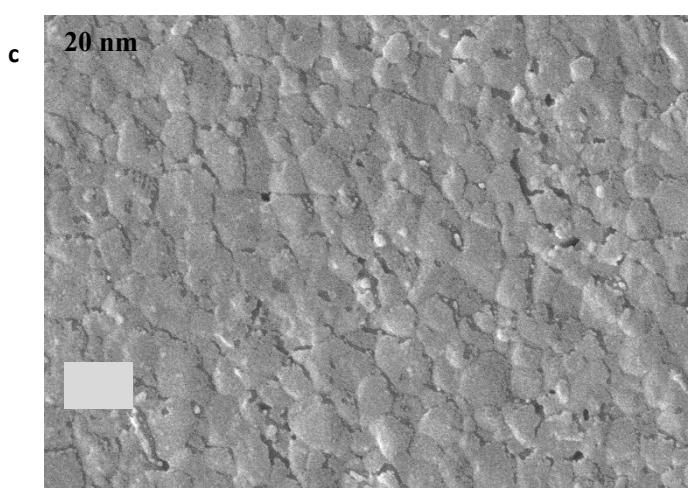
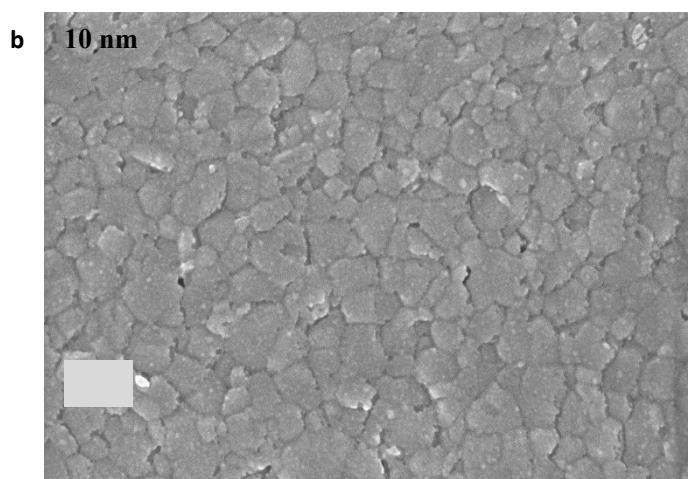
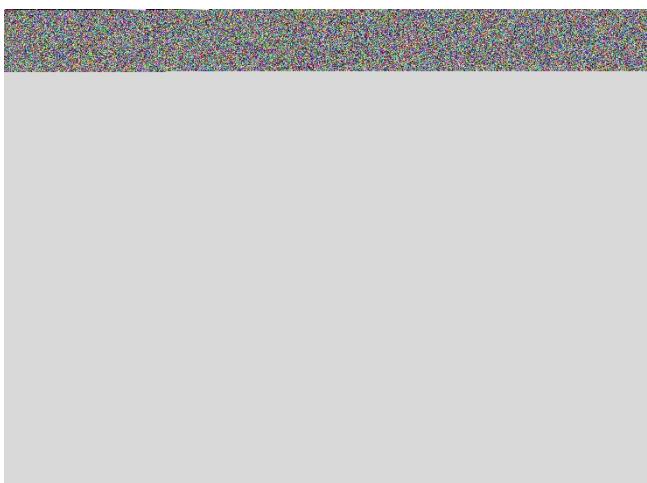


Figure S1 Absolute XRD of perovskite films on different thicknesses of C_{60} layer

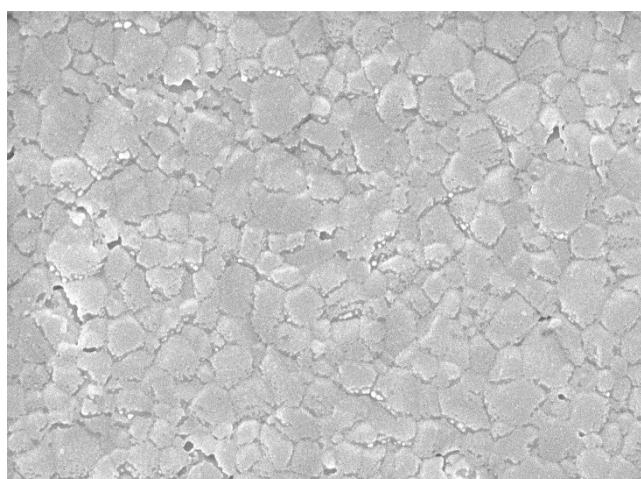
a

5 nm



30 nm

d



e

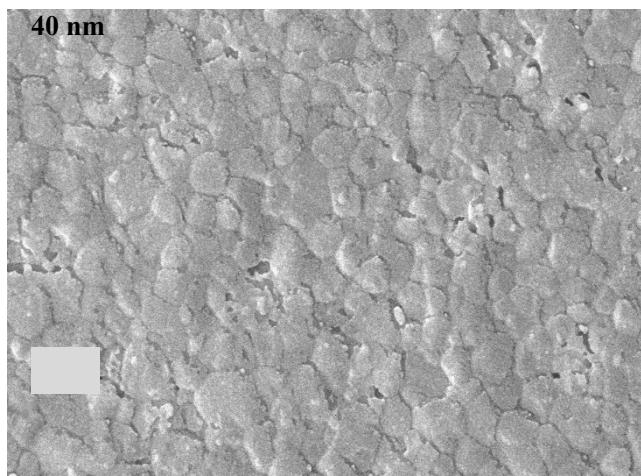


Figure S2 a-e SEM of perovskite films on different thicknesses of C₆₀ layer

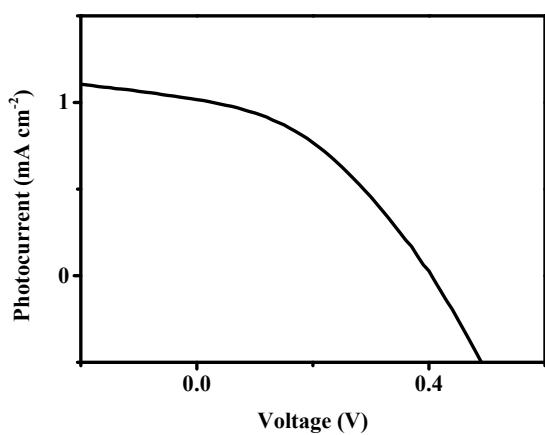


Figure S3 Current density vs. voltage curves of perovskite solar cells without C₆₀

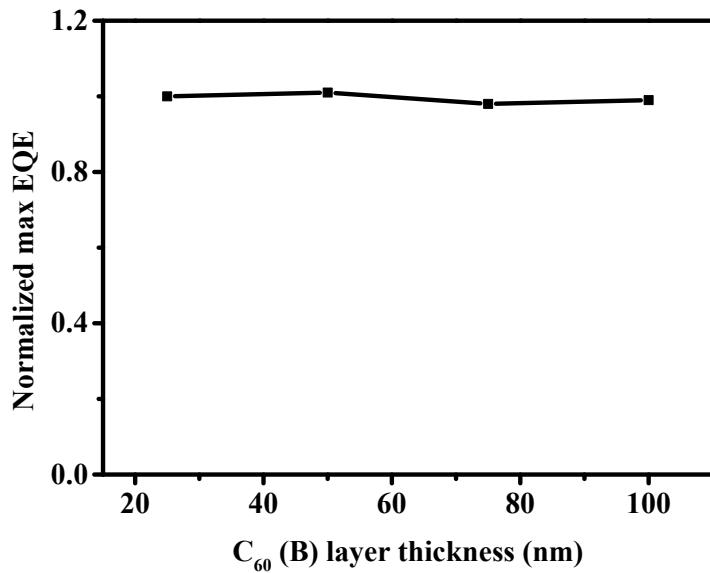


Figure S4 Normalized EQE of PDs with different thicknesses of C₆₀ (B) (@ 550 nm and -5V)